



INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁶ : C30B 23/02, 25/14, 35/00		A1	(11) International Publication Number: WO 99/07924
			(43) International Publication Date: 18 February 1999 (18.02.99)
(21) International Application Number: PCT/US98/16355		(74) Agent: HULTQUIST, Steven, J.; Intellectual Property/Technology Law, P.O. Box 14329, Research Triangle Park, NC 27709 (US).	
(22) International Filing Date: 5 August 1998 (05.08.98)			
(30) Priority Data: 08/906,039 5 August 1997 (05.08.97) US		(81) Designated States: AL, AM, AT, AU, AZ, BA, BE, BG, BR, BY, CA, CH, CN, CU, CZ, DE, DK, EE, ES, FI, GB, GE, GH, HU, IL, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, UA, UG, US, UZ, VN, YU, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).	
(63) Related by Continuation (CON) or Continuation-in-Part (CIP) to Earlier Application US 08/906,039 (CIP) Filed on 5 August 1997 (05.08.97)			
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(54) Title: APPARATUS AND METHOD FOR THE IN-SITU GENERATION OF DOPANTS

(57) Abstract

A method and apparatus for generating a dopant gas species which is a reaction product of a metal and a gas reactive therewith to form the dopant gas species. A source mass of metal (16) is provided and contacted with the reactive gas to yield a dopant gas species. The dopant gas species may be passed to a chemical vapor deposition reactor (320), or flowed to an ionization chamber (46) to generate ionic species for ion implantation.

